

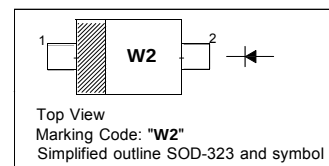
Silicon Epitaxial Planar Switching Diode

Features

- Ultra high speed switching application
- Low forward voltage
- Fast reverse recovery time
- Small total capacitance

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	80	V
Peak Reverse Voltage	V_{RM}	85	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Peak Forward Current	I_{FM}	300	mA
Surge Forward Current (10 ms)	I_{FSM}	2	A
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^{\circ}\text{C}$

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 100\text{ mA}$	V_F	1.2	V
Reverse Current at $V_R = 80\text{ V}$	I_R	0.5	μA
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	4	pF
Reverse Recovery Time at $I_F = I_R = 10\text{ mA}$, $I_{rr} = 0.1 \times I_R$, $R_L = 100\text{ }\Omega$	t_{rr}	4	ns

Fig. 1 I_F - V_F

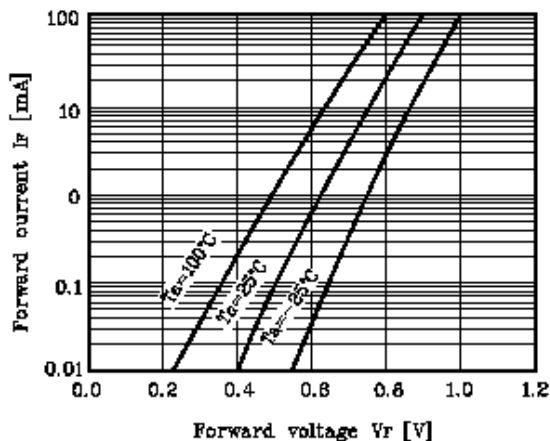


Fig. 2 I_R - V_R

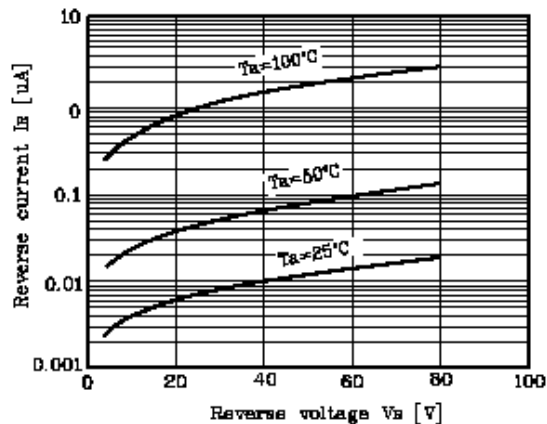


Fig. 3 C_T - V_R

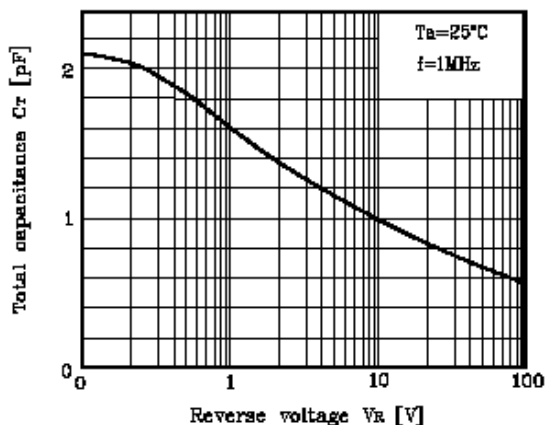


Fig. 4 t_{rr} - I_F

